

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| S50 9 | 40 | ((buried adj (insulating or insulation or isolation or oxide)) with substrate with (distance or thickness or thick) with (angstrom or ang or nm or nanometers)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 18:13 |
| S51 0 | 13 | ((buried adj (insulating or insulation or isolation or oxide)) with substrate with (distance or thickness or thick) with (angstrom or ang or nm or nanometers) with surface).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 18:14 |
| S51 1 | 80 | ((buried adj (insulating or insulation or isolation or oxide)) with substrate with (distance or thickness or thick) with (angstrom or ang or nm or nanometers) with surface) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 18:16 |
| S51 2 | 46 | ((buried adj (insulating or insulation or isolation or oxide)) near10 substrate near10 (distance or thickness or thick) near10 (angstrom or ang or nm or nanometers) near10 surface) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:38 |
| S51 3 | 83 | (depth or distance) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator) adj (layer or film)) near5 (thick or thickness) near5 substrate near5 surface | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:43 |
| S51 4 | 93 | (depth or distance) near5 (buried (insulating or dielectric or oxide or dioxide or insulation or insulator) adj (layer or film)) near5 (thick or thickness) near5 substrate near5 surface | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:43 |
| S51 5 | 5 | (depth or distance) near5 (buried near (insulating or dielectric or oxide or dioxide or insulation or insulator) adj (layer or film)) near5 (thick or thickness) near5 substrate near5 surface | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:44 |
| S51 6 | 12 | (depth or distance) near10 (buried near (insulating or dielectric or oxide or dioxide or insulation or insulator) adj (layer or film)) near10 (thick or thickness) near10 substrate near10 surface | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:47 |

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| S51 7 | 32 | (depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:49 |
| S51 8 | 12 | (depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and (substrate near5 (thick or thickness) near5 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:50 |
| S51 9 | 11 | (depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and (substrate near5 (thick or thickness) near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:50 |
| S52 0 | 3 | (depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and (substrate near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:51 |
| S52 1 | 3 | (depth near5 (buried adj (oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near5 (nm or nanometers or angstrom or ang) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:51 |
| S52 2 | 9 | ((distance or depth) near2 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric))) near2 (nm or nanometers or angstrom or ang) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:52 |

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|----------|----|---|---|----|----|------------------|
| S52 3 | 20 | ((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric)) near5 (nm or nanometers or angstrom or ang) near5 surface) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:52 |
| S52 4 | 11 | ((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric)) near5 (nm or nanometers or angstrom or ang) near5 surface near5 substrate) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:54 |
| S52 5 | 7 | ((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer)) near5 (nm or nanometers or angstrom or ang) near5 surface near5 substrate) and ((wafer or substrate) near2 (thick or thickness) near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:54 |
| S52 6 | 21 | ((distance or depth) near5 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer)) near5 (nm or nanometers or angstrom or ang) near5 surface near5 substrate) and ((wafer or substrate) near5 (thick or thickness) near5 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:55 |
| S52 7 | 82 | ((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer)) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near5 (thick or thickness) near5 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:56 |

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|----------|-----|--|---|----|----|------------------|
| S52 8 | 163 | ((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:56 |
| S52 9 | 163 | ((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang)) and (((dielectric or insulation or insulating or oxide or dioxide or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:57 |
| S53 0 | 151 | ((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang)) and (((dielectric or insulation or insulating or oxide or dioxide or insulator) near (layer or film))) near10 (thick or thickness) near5 (angstrom or ang or nanometer or nm)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:00 |

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|----------|------|--|---|----|----|------------------|
| S53 1 | 3 | ((((distance or depth) near10 ((oxide or dioxide or insulating or insulator or insulation or isolation or dielectric) adj (film or layer))) near10 (nm or nanometers or angstrom or ang) near10 surface near10 substrate) and ((wafer or substrate) near10 (thick or thickness) near10 (nanometer or nm or angstrom or ang)) and (((dielectric or insulation or insulating or oxide or dioxide or insulator) near (layer or film)) near10 (thick or thickness) near5 (angstrom or ang or nanometer or nm))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 12:58 |
| S53 2 | 4734 | (buried adj (oxide or dioxide) adj (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:03 |
| S53 3 | 684 | (thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:13 |
| S53 4 | 141 | (thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:20 |
| S53 5 | 20 | (thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang) and ((thick or thickness) near substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:22 |
| S53 6 | 0 | (thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang) and ((thick or thickness) near substrate near (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:22 |
| S53 7 | 10 | (thickness or thick) near2 (buried adj (oxide or dioxide) adj (layer or film)) near2 (nanometers or nm or angstrom or ang) and ((thick or thickness) near2 substrate near2 (nanometer or nm or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:23 |

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|----------|------|--|---|----|----|------------------|
| S53 8 | 436 | ((thick or thickness) near (substrate) near (angstrom or ang or nanometer or nm)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:24 |
| S53 9 | 35 | ((thick or thickness) near (substrate) near (angstrom or ang or nanometer or nm)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:25 |
| S54 0 | 6959 | ((thick or thickness) near (substrate)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:25 |
| S54 1 | 546 | ((thick or thickness) near (substrate)).clm. and ((thick or thickness) near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:25 |
| S54 2 | 152 | ((thick or thickness) near (substrate)).clm. and ((thick or thickness) near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:27 |
| S54 3 | 0 | ((thick or thickness) near (substrate)).clm. and ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:27 |
| S54 4 | 25 | ((thick or thickness) near (substrate)) same ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:27 |
| S54 5 | 21 | ((thick or thickness) near (substrate)) with ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:29 |
| S54 6 | 109 | ((thick or thickness) near (substrate)) and ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:31 |

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|----------|-------|---|---|----|----|------------------|
| S54 7 | 150 | ((thick or thickness) near (substrate or wafer)) and ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:31 |
| S54 8 | 27 | ((thick or thickness) near (substrate or wafer)) near10 ((thick or thickness) near buried near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:32 |
| S54 9 | 444 | ((thick or thickness) near (substrate or wafer)) near10 ((thick or thickness) near (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:34 |
| S55 0 | 17089 | ((thick or thickness or distance) near5 (substrate or wafer)) near10 ((thick or thickness or distance) near5 (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:34 |
| S55 1 | 80 | ((thick or thickness or distance) near5 (substrate or wafer)) near10 ((thick or thickness or distance) near5 (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:36 |
| S55 2 | 25 | ((thick or thickness or distance) near5 (substrate or wafer)) near10 ((thick or thickness or distance) near5 (oxide or insulating or dioxide or dielectric or insulation or insulator) near (layer or film)) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping)) and (micrometer or meter or angstrom or ang or nanometer or nm).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:38 |

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|--|---|--|---|----|----|------------------|
| S55 3 | 285 | (US-20010015168-\$ or US-20020005562-\$ or US-20020121661-\$ or US-20020127820-\$ or US-20030020068-\$ or US-20030080377-\$ or US-20030104681-\$ or US-20040007741-\$ or US-20040032005-\$ or US-20050269597-\$ or US-20050272207-\$ or US-20050272230-\$ or US-20020009837-\$ or US-20010000411-\$ or US-20020142507-\$ or US-20020158291-\$ or US-20030104658-\$ or US-20030211711-\$ or US-20040023430-\$ or US-20040070051-\$ or US-20040145000-\$ or US-20040214394-\$ or US-20050087811-\$ or US-20050116289-\$ or US-20050118826-\$).did. or (US-3508980-\$ or US-3897274-\$ or US-3933540-\$ or US-4005468-\$ or US-4109270-\$ or US-4272880-\$ or US-4432006-\$ or US-4601779-\$ or US-4651001-\$ or US-4662956-\$ or US-4667392-\$ or US-4679306-\$ or US-4712152-\$ or US-4717677-\$ or US-4746963-\$ or US-4771016-\$ or US-4774556-\$ or US-4785343-\$ or US-4789642-\$ or US-4851078-\$ or US-4851363-\$ or US-4853343-\$ or US-4870475-\$ or US-4871685-\$ or US-4897362-\$ or US-4899204-\$).did. or (US-4925809-\$ or US-4939568-\$ or US-4963505-\$ or US-4997786-\$ or US-5013681-\$ or US-5025304-\$ or US-5034343-\$ or US-5061652-\$ or US-5100830-\$ or US-5102821-\$ or US-5116771-\$ or US-5123975-\$ or US-5159429-\$ or US-5168078-\$ or US-5200348-\$ or US-5212397-\$ or US-5227653-\$ or US-5227660-\$ or US-5234535-\$ or US-5234846-\$ or US-5243209-\$ or US-5248633-\$ or US-5264395-\$ or US-5277748-\$ or US-5279978-\$ or US-5296385-\$ or US-5308788-\$).did. or (US-5310451-\$ or US-5315144-\$ or US-5321298-\$ or US-5324678-\$ or US-5340435-\$ or US-5344524-\$ or US-5344785-\$ or US-5352341-\$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2006/01/27 13:38 |
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| C:\Documents and Settings\ERdem\My Documents\FAST\workspaces\10602673_case.wsp | Or US-5365877-\$ or US-5366923-\$ Or US-5366924-\$ or US-5372952-\$ Or US-5374581-\$ or US-5376560-\$ | | | | | |

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|----------|-----|---|---|----|----|------------------|
| S55 4 | 7 | S553 and ((semiconductor adj substrate) near2 (thick or thickness)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:43 |
| S55 5 | 17 | S553 and ((semiconductor adj substrate) near2 (thick or thickness)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:44 |
| S55 6 | 917 | ((semiconductor adj substrate) near2 (thick or thickness)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:44 |
| S55 7 | 391 | (oxide or insulating or insulation or dielectric or insulator) with ((semiconductor adj substrate) near2 (thick or thickness)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:45 |
| S55 8 | 326 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) with ((semiconductor adj substrate) near2 (thick or thickness)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:46 |
| S55 9 | 305 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:46 |
| S56 0 | 2 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 order).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:47 |
| S56 1 | 2 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percen or order)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:47 |
| S56 2 | 34 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percen or order)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:47 |

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| S56 3 | 35 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percent or order)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:49 |
| S56 4 | 3 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) near10 (percentage or percent or order)), clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:48 |
| S56 5 | 2 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:49 |
| S56 6 | 2 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) with ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:49 |
| S56 7 | 250 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) with ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:50 |
| S56 8 | 188 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:50 |

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|----------|------|---|---|----|----|------------------|
| S56 9 | 4 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:51 |
| S57 0 | 188 | ((oxide or insulating or insulation or dielectric or insulator) near (layer or film)) near10 ((semiconductor adj substrate) near2 (thick or thickness) and (autodope or auto-dope or autodoping or auto-doping or (auto near dope) or (auto near doping or wafer))). | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:52 |
| S57 1 | 1617 | (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near (film or layer))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:54 |

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|----------------|--------------------|--|---|----|----|------------------|
| S57 2 | 285 | (US-20010015168-\$ or US-20020005562-\$ or US-20020121661-\$ or US-20020127820-\$ or US-20030020068-\$ or US-20030080377-\$ or US-20030104681-\$ or US-20040007741-\$ or US-20040032005-\$ or US-20050269597-\$ or US-20050272207-\$ or US-20050272230-\$ or US-20020009837-\$ or US-20010000411-\$ or US-20020142507-\$ or US-20020158291-\$ or US-20030104658-\$ or US-20030211711-\$ or US-20040023430-\$ or US-20040070051-\$ or US-20040145000-\$ or US-20040214394-\$ or US-20050087811-\$ or US-20050116289-\$ or US-20050118826-\$).did. or (US-3508980-\$ or US-3897274-\$ or US-3933540-\$ or US-4005468-\$ or US-4109270-\$ or US-4272880-\$ or US-4432006-\$ or US-4601779-\$ or US-4651001-\$ or US-4662956-\$ or US-4667392-\$ or US-4679306-\$ or US-4712152-\$ or US-4717677-\$ or US-4746963-\$ or US-4771016-\$ or US-4774556-\$ or US-4785343-\$ or US-4789642-\$ or US-4851078-\$ or US-4851363-\$ or US-4853343-\$ or US-4870475-\$ or US-4871685-\$ or US-4897362-\$ or US-4899204-\$).did. or (US-4925809-\$ or US-4939568-\$ or US-4963505-\$ or US-4997786-\$ or US-5013681-\$ or US-5025304-\$ or US-5034343-\$ or US-5061652-\$ or US-5100830-\$ or US-5102821-\$ or US-5116771-\$ or US-5123975-\$ or US-5159429-\$ or US-5168078-\$ or US-5200348-\$ or US-5212397-\$ or US-5227653-\$ or US-5227660-\$ or US-5234535-\$ or US-5234846-\$ or US-5243209-\$ or US-5248633-\$ or US-5264395-\$ or US-5277748-\$ or US-5279978-\$ or US-5296385-\$ or US-5308788-\$).did. or (US-5310451-\$ or US-5315144-\$ or US-5321298-\$ or US-5324678-\$ or US-5340435-\$ or US-5344524-\$ or US-5344785-\$ or US-5352341-\$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2006/01/27 13:53 |
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| S57 3 | 15 | S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near (film or layer))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:55 |
| S57 4 | 0 | S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near (film or layer) near (nm or angstrom or nanometer or ang))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:55 |
| S57 5 | 0 | S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near2 (film or layer) near (nm or angstrom or nanometer or ang))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:55 |
| S57 6 | 0 | S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near2 (film or layer) near (nm or angstrom or nanometer or ang))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:55 |
| S57 7 | 6 | S572 and (depth near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near2 (film or layer) near2 (nm or angstrom or nanometer or ang))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:56 |
| S57 8 | 1 | S572 and (depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:57 |
| S57 9 | 230 | (depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 13:57 |
| S58 0 | 25 | (depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:26 |
| S58 1 | 230 | (depth near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:27 |

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|----------|------|--|---|----|----|------------------|
| S58 2 | 274 | ((distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) near5 (nm or angstrom or nanometer or ang))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:28 |
| S58 3 | 8288 | ((distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near10 (film or layer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:33 |
| S58 4 | 4991 | (distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near10 (film or layer) and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:33 |
| S58 5 | 2383 | (distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near10 (film or layer) and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film)) near5 (angstrom or ang or nanometer or nm))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:34 |
| S58 6 | 524 | (distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:35 |
| S58 7 | 41 | (distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator) near5 (film or layer) and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:35 |

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|----------|-----|--|---|----|----|------------------|
| S58 8 | 7 | ((distance or depth) near5 surface near5 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near5 (film or layer)).clm. and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:36 |
| S58 9 | 14 | ((distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer)).clm. and ((thickness or thick) near2 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near2 (layer or film)) near2 (angstrom or ang or nanometer or nm)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:36 |
| S59 0 | 131 | ((distance or depth) near10 surface near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer)).clm. and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film)) near5 (angstrom or ang or nanometer or nm)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:37 |
| S59 1 | 73 | ((distance or depth) near10 ((first or second or upper or lower or top or bottom or main or reverse) near surface) near10 ((oxide or dielectric or insulating or insulation or dioxide or isolation or insulator)) near10 (film or layer)).clm. and ((thickness or thick) near5 ((oxide or dielectric or insulating or insulation or insulator or dioxide) near5 (layer or film)) near5 (angstrom or ang or nanometer or nm)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:39 |
| S59 2 | 0 | (distance near between near ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:41 |

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|----------|-----|---|---|----|----|------------------|
| S59 3 | 0 | (distance near between near2 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:41 |
| S59 4 | 0 | (distance near between near3 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:41 |
| S59 5 | 0 | (distance near between near3 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near3 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:41 |
| S59 6 | 0 | (distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near3 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:41 |
| S59 7 | 0 | (distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near furface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:42 |
| S59 8 | 173 | (distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:43 |

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|----------|----|--|---|----|----|------------------|
| S59 9 | 65 | (distance near between near2 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near2 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:43 |
| S60 0 | 70 | (distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:44 |
| S60 1 | 2 | (distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near5 (silicon adj substrate)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:45 |
| S60 2 | 6 | (distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near5 (semiconductor adj substrate)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:46 |
| S60 3 | 9 | (distance near between near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near5 (semiconductor adj substrate)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:47 |
| S60 4 | 27 | (distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near10 (semiconductor adj substrate)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:47 |

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|----------|-----|---|---|----|----|------------------|
| S60 5 | 0 | (distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near10 (buried adj (oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near10 (semiconductor adj substrate)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:48 |
| S60 6 | 2 | (distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface) near10 (buried adj (oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film)) near10 (substrate)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:49 |
| S60 7 | 2 | (distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 (buried adj (oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:50 |
| S60 8 | 49 | (distance near between near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:50 |
| S60 9 | 394 | ((distance or depth) near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:51 |
| S61 0 | 111 | (((distance or depth) near10 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:51 |

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|----------|-------|--|---|----|----|------------------|
| S61 1 | 77 | ((distance or depth) near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near10 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:51 |
| S61 2 | 45 | ((distance or depth) near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 substrate) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:53 |
| S61 3 | 21 | ((distance or depth) near5 ((upper or top or bottom or bottom or first or second or main or reverse or opposite or front) near surface near2 ((silicon or semiconductor) adj substrate)) near5 ((oxide or insulating or dielectric or dioxide or insulation or insulator) near (layer or film))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:55 |
| S61 4 | 17297 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:56 |
| S61 5 | 4955 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:56 |
| S61 6 | 1 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and 10/602673 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:57 |

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|----------|------|--|---|----|----|------------------|
| S61 7 | 30 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and (autodope or autodoping or auto-dope or auto-doping or (auto near dope) or (auto near doping)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 14:57 |
| S61 8 | 20 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and (autodope or autodoping or auto-dope or auto-doping or (auto near dope) or (auto near doping)) and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:00 |
| S61 9 | 1533 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:02 |
| S62 0 | 651 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)).clm. and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:03 |
| S62 1 | 97 | (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)).clm. and wafer.ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:06 |

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|----------|-----|---|---|----|----|------------------|
| S62 2 | 1 | distance near between near2 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:06 |
| S62 3 | 11 | distance near between near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:08 |
| S62 4 | 20 | distance near between near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:10 |
| S62 5 | 16 | distance near between near5 ((reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface) near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:09 |
| S62 6 | 193 | (depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:10 |

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|----------|----|--|---|----|----|------------------|
| S62 7 | 45 | ((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:15 |
| S62 8 | 34 | ((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and (angstrom or ang or nanometer or nm) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:16 |
| S62 9 | 18 | ((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and ((angstrom or ang or nanometer or nm) near5 substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:17 |
| S63 0 | 1 | ((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and ((angstrom or ang or nanometer or nm) near5 substrate) and (substrate near (thick or thickness)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:18 |

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|----------|---|---|---|----|----|------------------|
| S63 1 | 8 | ((depth or deep or distance) near5 (reverse or upper or lower or top or bottom or first or second or main or opposite or rear) near surface near5 ((semiconductor or silicon) near substrate) near5 ((insulating or dielectric or oxide or dioxide or insulation or insulator or isolation) near (layer or film))).clm. and ((angstrom or ang or nanometer or nm) near5 substrate) and (substrate near2 (thick or thickness)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:18 |
| S63 2 | 7 | ("5034335" "5233218" "5494846" "5512501" "5780888" "5869386" "6022765").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2006/01/27 15:37 |

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|--|---|--|---|----|----|------------------|
| S63 3 | 289 | (US-20010000411-\$ or US-20010015168-\$ or US-20020005562-\$ or US-20020009837-\$ or US-20020121661-\$ or US-20020127820-\$ or US-20020142507-\$ or US-20020158291-\$ or US-20030020068-\$ or US-20030080377-\$ or US-20030104658-\$ or US-20030104681-\$ or US-20030211711-\$ or US-20040007741-\$ or US-20040023430-\$ or US-20040032005-\$ or US-20040070051-\$ or US-20040145000-\$ or US-20040214394-\$ or US-20050087811-\$ or US-20050116289-\$ or US-20050118826-\$ or US-20050269597-\$ or US-20050272207-\$ or US-20050272230-\$).did. or (US-3508980-\$ or US-3897274-\$ or US-3933540-\$ or US-4005468-\$ or US-4109270-\$ or US-4272880-\$ or US-4432006-\$ or US-4601779-\$ or US-4651001-\$ or US-4662956-\$ or US-4667392-\$ or US-4679306-\$ or US-4712152-\$ or US-4717677-\$ or US-4746963-\$ or US-4771016-\$ or US-4774556-\$ or US-4785343-\$ or US-4789642-\$ or US-4851078-\$ or US-4851363-\$ or US-4853343-\$ or US-4870475-\$ or US-4871685-\$ or US-4897362-\$ or US-4899204-\$).did. or (US-4925809-\$ or US-4939568-\$ or US-4963505-\$ or US-4997786-\$ or US-5013681-\$ or US-5025304-\$ or US-5034343-\$ or US-5061652-\$ or US-5100830-\$ or US-5102821-\$ or US-5116771-\$ or US-5123975-\$ or US-5159429-\$ or US-5168078-\$ or US-5200348-\$ or US-5212397-\$ or US-5227653-\$ or US-5227660-\$ or US-5234535-\$ or US-5234846-\$ or US-5243209-\$ or US-5248633-\$ or US-5264395-\$ or US-5277748-\$ or US-5279978-\$ or US-5296385-\$ or US-5308788-\$).did. or (US-5310451-\$ or US-5315144-\$ or US-5321298-\$ or US-5324678-\$ or US-5340435-\$ or US-5344524-\$ or US-5344785-\$ or US-5352341-\$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2006/01/27 15:45 |
| Search History C:\Documents and Settings\ERdem\My Documents\FAST\workspaces\10602673_case.wsp | 1/27/06 5:50:37 PM Page 24 or US-5365877-\$ or US-5366923-\$ or US-5366924-\$ or US-5372952-\$ or US-5274591-\$ or US-5276560-\$ | | | | | |

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|----------|-----|--|---|----|----|------------------|
| S63 4 | 130 | S633 and (substrate near5 (thick or thickness)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:50 |
| S63 5 | 29 | S633 and (substrate near5 (thick or thickness) near5 (nm or nanometer or micrometer or angstrom or ang)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:53 |
| S63 6 | 65 | S633 and (substrate near2 (thick or thickness)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 16:00 |
| S63 7 | 0 | S633 and (substrate near2 (thick or thickness) near2 ".mu.m") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:56 |
| S63 8 | 0 | S633 and (substrate near2 (thick or thickness) near2 mu) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 15:56 |
| S63 9 | 130 | S633 and (substrate near5 (thick or thickness)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/27 16:00 |